Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	100	chidambarrao near dureseti.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 18:41
L2	98	dokumaci near omer.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 18:41
L3	255	438/142.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 18:41
L4	173824	"438"/$.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 18:41
L5	1	(semiconductor near structure) and (source) and (drain) and (channel near structure) and (channel near fin) and (vertical near fin) and (t-shaped) and (gate near dielectric) and (gate near electrode).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 18:44
L6	2	(semiconductor near structure) and (source) and (drain) and (channel near structure) and (channel near fin) and (vertical near fin) and (t-shaped) and (gate near dielectric) and (gate near electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 18:44
L7	2	(semiconductor) and (source) and (drain) and (channel near structure) and (channel near fin) and (vertical near fin) and (t-shaped) and (gate near dielectric) and (gate near electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 18:44
L8	3	(semiconductor) and (source) and (drain) and (channel) and (channel near fin) and (vertical near fin) and (t-shaped) and (gate near dielectric) and (gate near electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 18:49

L9	3	(source) and (drain) and (channel) and (channel near fin) and (vertical near fin) and (t-shaped) and (gate near dielectric) and (gate near electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 18:49
L10	3	(source) and (drain) and (channel near fin) and (vertical near fin) and (t-shaped) and (gate near dielectric) and (gate near electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 18:50
L11	3	(source) and (drain) and (channel near fin) and (vertical near fin) and (t-shaped) and (dielectric) and (electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 18:50
L12	7	(source) and (drain) and (channel near3 fin) and (vertical near3 fin) and (t-shaped) and (dielectric) and (electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 18:55
L13	5	(source) and (drain) and (horizontal) near3 (channel or fin) and (vertical) near3 (fin or channel) and (t-shaped) and (dielectric) and (electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 18:56
L14	5	(source) and (drain) and ((horizontal) near3 (channel or fin)) and (vertical) near3 (fin or channel) and (t-shaped) and (dielectric) and (electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 18:56
L15	53	(source) and (drain) and ((vertical) near3 (channel or fin)) and (t-shaped) and (dielectric) and (electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 18:57
L16	48	(source) and (drain) and ((vertical) near3 (channel or fin)) and (t-shaped) and (dielectric) and (gate near electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 18:57
L17	34	(source) and (drain) and ((vertical) near3 (channel or fin)) and (t-shaped) and (gate near dielectric) and (gate near electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 18:59
L18	5	(source) and (drain) and ((vertical) near (channel or fin)) and (t-shaped) and (gate near dielectric) and (gate near electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 18:57

L19	6	(source) and (drain) and ((vertical) near3 (fin)) and (t-shaped) and (gate near dielectric) and (gate near electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 19:00
L20	9	(source) and (drain) and ((vertical) near3 (fin)) and (t-shaped) and (dielectric or insulat$3) and (gate near electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 20:05
L21	139	(source) and (drain) and ((vertical) near3 (fin)) and (dielectric or insulat$3) and (gate near electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 19:19
L22	82	4 and 21	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 19:19
L23	260	(source) and (drain) and ((channel) near10 (fin)) and (dielectric or insulat$3) and (gate near electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 19:19
L24	222	(source) and (drain) and ((channel) near10 (fin)) and ((gate) near (dielectric or insulat$3)) and (gate near electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 19:19
L25	139	(source) and (drain) and ((channel) near10 (fin)) and (gate) near (dielectric) and (gate near electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 19:19
L26	76	4 and 25	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 19:19
L27	1291	(vertical near5 fin) and (horizontal near5 fin)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 20:14
L28	69	(channel) with (vertical near5 fin) and (horizontal near5 fin)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 20:14

L29	2	4 and 28	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 20:06
L30	335	(channel) and (vertical near5 fin) and (horizontal near5 fin)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 20:06
L31	14	4 and 30	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 20:07
L32	531	finfet	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 20:08
L33	16	27 and 32	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 20:13
L34	1	(t-fin near channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 20:13
L35	2484	(t-shaped near5 channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 20:13
L36	1001	(t-shaped near channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 20:13
L37	0	27 and 36	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 20:14
L38	4	27 and t-fin	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 20:14

L39	32	(channel) with (vertical near5 fin) and (planar near5 fin)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 20:29
L40	2	39 and t-fin	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 20:15
L41	173	(channel) same ((vertical near10 fin)) and ((planar or horizontal) near5 (fin))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 20:20
L42	26	41 and (source) with (drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 20:20
L43	11	(semiconductor) with (vertical near5 fin) and (planar near5 fin)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 20:33
L44	225	(semiconductor) with (fin near15 channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 20:33
L45	143	44 and (source near15 drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 20:33
L46	57	4 and 45	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 20:33
L47	44	46 and finfet	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/03 20:33